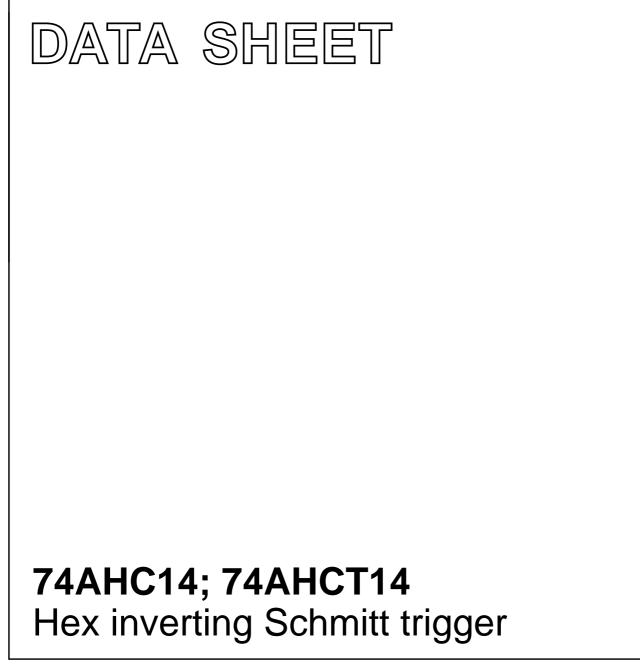
INTEGRATED CIRCUITS



Product specification Supersedes data of 1999 Sep 27 2003 May 26



74AHC14; 74AHCT14

FEATURES

- Balanced propagation delays
- Inputs accepts voltages higher than $V_{\mbox{\scriptsize CC}}$
- For 74AHC only: operates with CMOS input levels
- For 74AHCT only: operates with TTL input levels
- ESD protection: HBM EIA/JESD22-A114-A exceeds 2000 V MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from -40 to +85 °C and -40 to +125 °C.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25 \text{ °C}$; $t_r = t_f \le 3.0 \text{ ns.}$

DESCRIPTION

The 74AHC14 and 74AHCT14 are high-speed Si-gate CMOS devices and are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard No. 7A.

The 74AHC14 and 74AHCT14 provide six inverting buffers with Schmitt-trigger action. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

SYMBOL	PARAMETER	CONDITIONS	ТҮР	UNIT	
STWBOL	FARAMETER	CONDITIONS	AHC	АНСТ	
t _{PHL} /t _{PLH}	propagation delay nA to nY	C _L = 15 pF; V _{CC} = 5 V	3.2	4.0	ns
C ₁	input capacitance	$V_{I} = V_{CC}$ or GND	3.0	3.0	pF
Co	output capacitance		4.0	4.0	pF
C _{PD}	power dissipation capacitance per buffer	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ notes 1 and 2	10	12	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

2. The condition is $V_1 = GND$ to V_{CC} .

FUNCTION TABLE

See note 1.

INPUT	OUTPUT
nA	nY
L	Н
Н	L

Note

1. H = HIGH voltage level;

L = LOW voltage level.

74AHC14; 74AHCT14

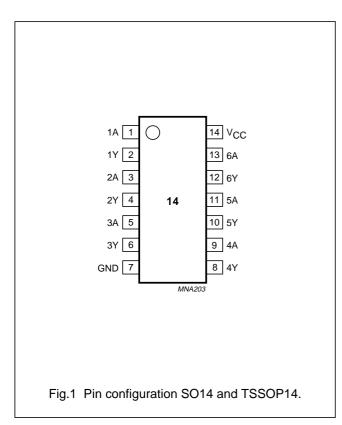
ORDERING INFORMATION

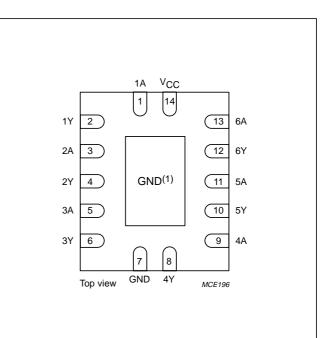
			PACKAGE		
TYPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE
74AHC14D	–40 to +125 °C	14	SO14	plastic	SOT108-1
74AHCT14D	–40 to +125 °C	14	SO14	plastic	SOT108-1
74AHC14PW	–40 to +125 °C	14	TSSOP14	plastic	SOT402-1
74AHCT14PW	–40 to +125 °C	14	TSSOP14	plastic	SOT402-1
74AHC14BQ	–40 to +125 °C	14	DHVQFN14	plastic	SOT762-1
74AHCT14BQ	–40 to +125 °C	14	DHVQFN14	plastic	SOT762-1

PINNING

PIN	SYMBOL	DESCRIPTION
1	1A	data input
2	1Y	data output
3	2A	data input
4	2Y	data output
5	3A	data input
6	3Y	data output
7	GND	ground (0 V)

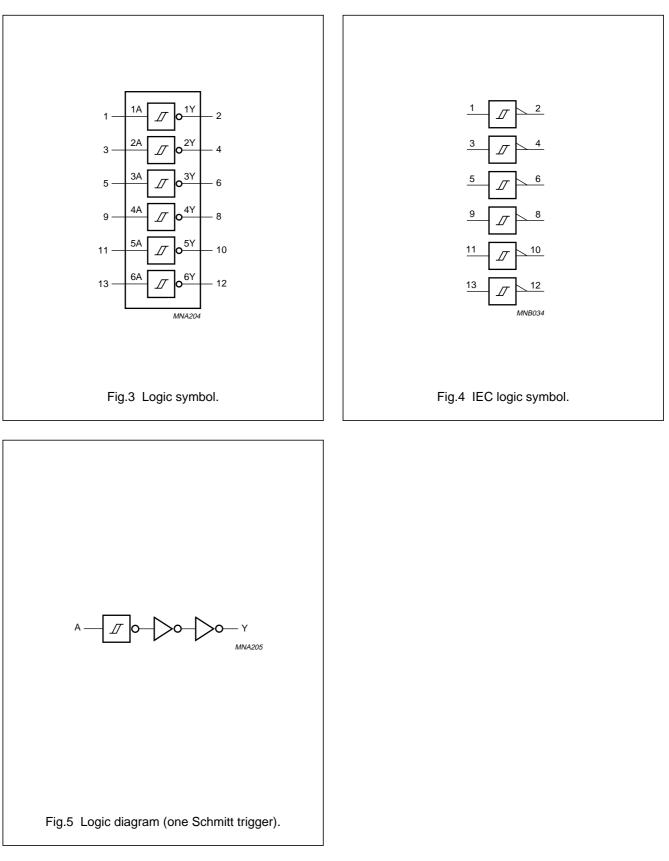
PIN	SYMBOL	DESCRIPTION
8	4Y	data output
9	4A	data input
10	5Y	data output
11	5A	data input
12	6Y	data output
13	6A	data input
14	V _{CC}	supply voltage





(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as a supply pin or input.

Fig.2 Pin configuration DHVQFN14.



74AHC14; 74AHCT14

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	74AHC			74AHCT			
STMBOL	FARAMETER	CONDITIONS	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	operating ambient temperature	see DC and AC	-	+25	-	_	+25	-	°C
		characteristics per	-40	-	+125	-40	-	+125	°C
		device	-40	_	+125	-40	-	+125	°C

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input diode current	V _I < -0.5 V; note 1	_	-20	mA
I _{ОК}	output diode current	$V_{\rm O}$ < -0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V; note 1	-	±20	mA
lo	output source or sink current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC} , I _{GND}	V _{CC} or GND current		-	±75	mA
T _{stg}	storage temperature		-65	+150	°C
PD	power dissipation	$T_{amb} = -40$ to +125 °C; note 2	-	500	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For SO14 packages: above 70 °C the value of P_D derates linearly with 8 mW/K.
For TSSOP14 packages: above 60 °C the value of P_D derates linearly with 5.5 mW/K.
For DHVQFN14 packages: above 60 °C the value of P_D derates linearly with 4.5 mW/K.

74AHC14; 74AHCT14

DC CHARACTERISTICS

Type 74AHC14

At recommended operating conditions; voltage are referenced to GND (ground = 0 V).

		TEST COND	ITIONS		T\/D		
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	MIN.	TYP.	MAX.	
T _{amb} = 25 °	C		I	-1	_	_	
V _{T+}	positive going threshold		3.0	-	-	2.2	V
			4.5	-	_	3.15	V
			5.5	-	_	3.85	V
V _{T-}	negative going		3.0	0.9	_	-	V
	threshold		4.5	1.35	_	_	V
			5.5	1.65	_	_	V
V _H	hysteresis (V _{T+} – V _{T-})		3.0	0.3	_	1.2	V
			4.5	0.4	_	1.4	V
			5.5	0.5	_	1.6	V
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL};$	2.0	1.9	2.0	_	V
	voltage; all outputs	$I_O = -50 \ \mu A$	3.0	2.9	3.0	_	V
			4.5	4.4	4.5	_	V
V _{OH}	HIGH-level output	$V_I = V_{IH} \text{ or } V_{IL}$					
	voltage	l _O = -4.0 mA	3.0	2.58	-	_	V
		I _O = -8.0 mA	4.5	3.94	-	-	V
V _{OL}	LOW-level output	$V_I = V_{IH} \text{ or } V_{IL};$	2.0	-	0	0.1	V
	voltage; all outputs	I _O = 50 μA	3.0	-	0	0.1	V
			4.5	-	0	0.1	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	voltage	I _O = 4.0 mA	3.0	-	-	0.36	V
		I _O = 8.0 mA	4.5	_	-	0.36	V
ILI	input leakage current	$V_I = V_{CC}$ or GND	5.5	_	-	0.1	μA
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	-	-	2.0	μΑ
CI	input capacitance			-	3	10	pF

	DADAMETER	TEST COND	ITIONS		TVP	MAX.	
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	MIN.	TYP.		
T _{amb} = -40	to +85 °C		I				
V _{T+}	positive going threshold		3.0	-	-	2.2	V
			4.5	_	_	3.15	V
			5.5	_	_	3.85	V
V _{T-}	negative going		3.0	0.9	_	_	V
	threshold		4.5	1.35	_	_	V
		5.5	1.65	_	_	V	
V _H	hysteresis (V _{T+} – V _{T–})		3.0	0.3	_	1.2	V
			4.5	0.4	_	1.4	V
			5.5	0.5	_	1.6	V
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL};$	2.0	1.9	_	_	V
	voltage; all outputs	I _O = –50 μA	3.0	2.9	_	_	V
			4.5	4.4	_	_	V
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	voltage	l _O = -4.0 mA	3.0	2.48	_	_	V
		l _O = -8.0 mA	4.5	3.8	_	_	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL};$	2.0	_	_	0.1	V
	voltage; all outputs	I _O = 50 μA	3.0	_	_	0.1	V
			4.5	_	_	0.1	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	voltage	I _O = 4.0 mA	3.0	_	_	0.44	V
		I _O = 8.0 mA	4.5	_	_	0.44	V
ILI	input leakage current	$V_{I} = V_{CC}$ or GND	5.5	_	_	1.0	μA
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	-	-	20	μA
CI	input capacitance			_	_	10	pF

		TEST COND	ITIONS		TYP.	MAX.	
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	MIN.			
T _{amb} = -40	to +125 °C				- I	-	
V _{T+}	positive going threshold		3.0	-	-	2.2	V
			4.5	_	_	3.15	V
			5.5	_	_	3.85	V
V _{T-}	negative going		3.0	0.9	_	_	V
	threshold		4.5	1.35	_	_	V
		5.5	1.65	_	_	V	
V _H	hysteresis (V _{T+} – V _{T-})		3.0	0.25	_	1.2	V
			4.5	0.35	_	1.4	V
			5.5	0.45	_	1.6	V
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL};$	2.0	1.9	_	_	V
	voltage; all outputs	I _O = –50 μA	3.0	2.9	_	_	V
			4.5	4.4	_	_	V
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	voltage	l _O = -4.0 mA	3.0	2.40	_	_	V
		l _O = -8.0 mA	4.5	3.70	_	_	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL};$	2.0	_	_	0.1	V
	voltage; all outputs	I _O = 50 μA	3.0	_	_	0.1	V
			4.5	_	_	0.1	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$					
	voltage	I _O = 4.0 mA	3.0	_	_	0.55	V
		I _O = 8.0 mA	4.5	_	_	0.55	V
I _{LI}	input leakage current	$V_{I} = V_{CC}$ or GND	5.5	_	_	2.0	μA
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	-	-	40	μA
CI	input capacitance			_	_	10	pF

74AHC14; 74AHCT14

Type 74AHCT14

At recommended operating conditions; voltage are referenced to GND (ground = 0 V).

		TEST CONDIT	IONS		TVD	MAY		
SYMBOL	PARAMETER	OTHER V _{CC} (V)		MIN.	TYP.	MAX.		
T _{amb} = 25 °	C							
V _{T+}	positive going threshold		4.5	_	-	1.9	V	
			5.5	-	_	2.1	V	
V _{T-}	negative going		4.5	0.5	-	-	V	
	threshold		5.5	0.6	-	-	V	
V _H	hysteresis (V _{T+} – V _{T-})		4.5	0.4	-	1.4	V	
			5.5	0.4	-	1.5	V	
V _{OH}	HIGH-level output voltage; all outputs	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -50 \ \mu\text{A}$	4.5	4.4	4.5	-	V	
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -8.0 \text{ mA}$	4.5	3.94	-	-	V	
V _{OL}	LOW-level output voltage; all outputs	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 50 \ \mu\text{A}$	4.5	-	0	0.1	V	
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 8 \text{ mA}$	4.5	-	-	0.36	V	
ILI	input leakage current	$V_I = V_{CC}$ or GND	5.5	-	_	0.1	μA	
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	-	-	2.0	μA	
ΔI_{CC}	additional quiescent supply current per input pin	$V_I = V_{CC} - 2.1 \text{ V other}$ inputs at V_{CC} or GND; $I_O = 0$	4.5 to 5.5	-	-	1.35	mA	
CI	input capacitance			-	3	10	pF	

		TEST CONDIT	IONS		TVD		
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	MIN.	TYP.	MAX.	
T _{amb} = -40	to +85 °C		-1	-1	_		
V _{T+}	positive going threshold		4.5	-	-	1.9	V
			5.5	_	_	2.1	V
V _{T-}	negative going		4.5	0.5	_	-	V
	threshold		5.5	0.6	_	_	V
V _H	hysteresis (V _{T+} – V _{T–})		4.5	0.4	_	1.4	V
			5.5	0.4	_	1.5	V
V _{OH}	HIGH-level output voltage; all outputs	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -50 \ \mu\text{A}$	4.5	4.4	-	-	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = -8.0 \text{ mA}$	4.5	3.8	-	-	V
V _{OL}	LOW-level output voltage; all outputs	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 50 \ \mu\text{A}$	4.5	-	-	0.1	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL};$ $I_O = 8 \text{ mA}$	4.5	-	-	0.44	V
ILI	input leakage current	$V_I = V_{CC}$ or GND	5.5	-	_	1.0	μA
I _{CC}	quiescent supply current	$V_1 = V_{CC}$ or GND; $I_0 = 0$	5.5	-	-	20	μΑ
ΔI_{CC}	additional quiescent supply current per input pin	$V_I = V_{CC} - 2.1 \text{ V other}$ inputs at V_{CC} or GND; $I_O = 0$	4.5 to 5.5	-	-	1.5	mA
CI	input capacitance			-	_	10	pF

	DADAMETER	TEST CONDITIONS						
SYMBOL	PARAMETER	OTHER V _{CC} (V)		MIN.	TYP.	MAX.		
T _{amb} = -40	to +125 °C			1			•	
V _{T+}	positive going threshold		4.5	_	-	1.9	V	
			5.5	-	_	2.1	V	
V _{T-}	negative going		4.5	0.5	_	_	V	
	threshold		5.5	0.6	_	_	V	
V _H	hysteresis (V _{T+} – V _{T-})		4.5	0.35	_	1.4	V	
			5.5	0.35	_	1.5	V	
V _{OH}	HIGH-level output voltage; all outputs	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -50 \ \mu\text{A}$	4.5	4.4	-	-	V	
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -8.0 \text{ mA}$	4.5	3.7	-	-	V	
V _{OL}	LOW-level output voltage; all outputs	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 50 \ \mu\text{A}$	4.5	-	-	0.1	V	
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 8 \text{ mA}$	4.5	-	-	0.55	V	
ILI	input leakage current	$V_{I} = V_{CC}$ or GND	5.5	-	_	2.0	μA	
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	-	-	40	μA	
Δl _{CC}	additional quiescent supply current per input pin	$V_I = V_{CC} - 2.1 \text{ V other}$ inputs at V_{CC} or GND; $I_O = 0$	4.5 to 5.5	-	-	1.5	mA	
CI	input capacitance			-	_	10	pF	

74AHC14; 74AHCT14

AC CHARACTERISTICS

Type 74AHC14

GND = 0 V; t_r = $t_f \le 3.0$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS						
		OTHER	C _L (pF)	V _{CC} (V)	MIN.	TYP.	MAX.	
T _{amb} = 25 °	C					-	-	
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 6 and 7 15 15 50	15	3.3	_	4.3	-	ns
			15	3.0 to 3.6	_	_	12.8	ns
			50	3.3	_	5.8	-	ns
			50	3.0 to 3.6	_	_	16.3	ns
			15	5.0	_	3.2	-	ns
			15	4.5 to 5.5	_	_	8.6	ns
			50	5.0	_	4.2	_	ns
			50	4.5 to 5.5	_	-	10.6	ns
T _{amb} = -40	to +85 °C	•						
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 6 and 7	15	3.0 to 3.6	1.0	-	15.0	ns
			50	3.0 to 3.6	1.0	_	18.0	ns
			15	4.5 to 5.5	1.0	_	10.0	ns
			50	4.5 to 5.5	1.0	-	12.0	ns
T _{amb} = -40	to +125 °C	•	•			•	•	
t _{PHL} /t _{PLH}	propagation delay nA to nY	l e	15	3.0 to 3.6	1.0	-	16.0	ns
			50	3.0 to 3.6	1.0	-	20.5	ns
			15	4.5 to 5.5	1.0	-	11.0	ns
			50	4.5 to 5.5	1.0	_	13.5	ns

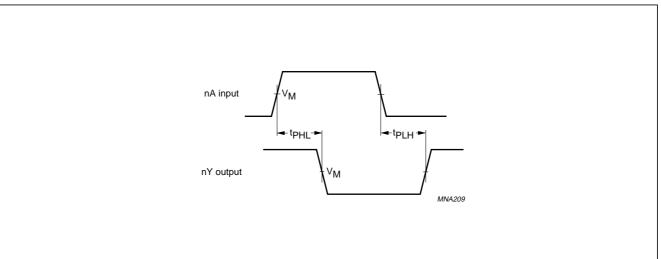
74AHC14; 74AHCT14

Type 74AHCT14

 $GND = 0 \text{ V}; t_r = t_f \leq 3.0 \text{ ns}.$

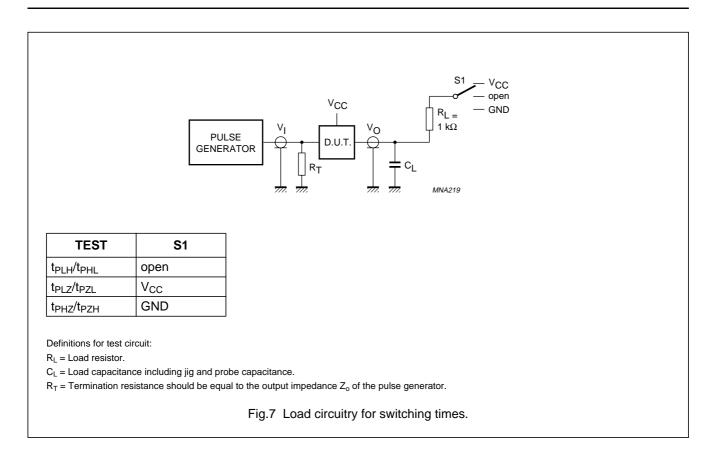
SYMBOL	PARAMETER	TEST CONDITIONS			MIN.	TYP.		
	PARAMETER	OTHER	C _L (pF)	V _{CC} (V)		ITP.	MAX.	UNIT
$T_{amb} = 25 \text{ °C}$								
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 6 and 7	15	5.0	_	4.0	-	ns
			15	4.5 to 5.5	_	-	7.0	ns
			50	5.0	-	5.4	-	ns
			50	4.5 to 5.5	-	-	8.0	ns
T _{amb} = -40 to +85 °C								
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 6 and 7	15	4.5 to 5.5	1.0	-	8.0	ns
			50	4.5 to 5.5	1.0	_	9.0	ns
T _{amb} = -40 to +125 °C								
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 6 and 7	15	4.5 to 5.5	1.0	-	9.0	ns
			50	4.5 to 5.5	1.0	_	10.0	ns

AC WAVEFORMS

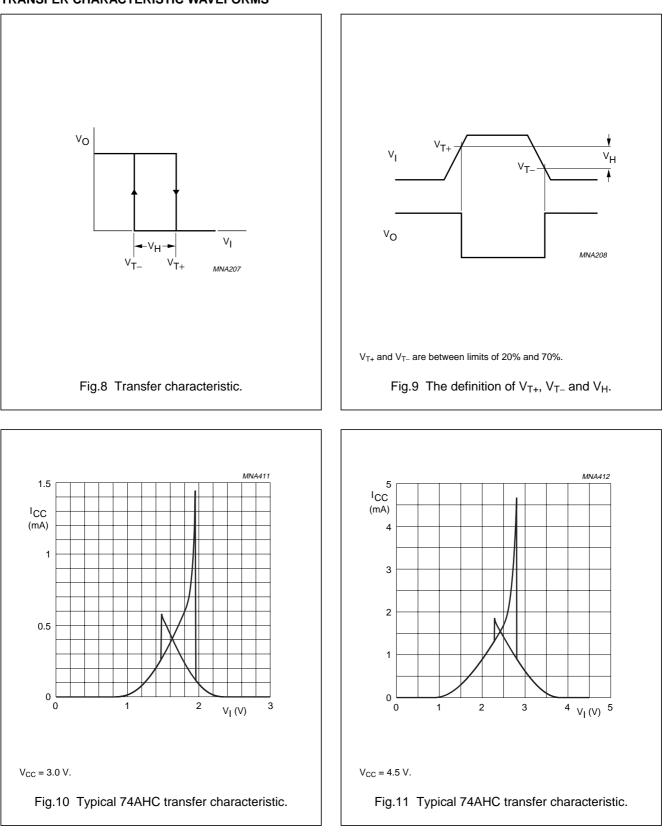


FAMILY	V _I INPUT REQUIREMENTS	V _M INPUT	V _M OUTPUT	
74AHC14	GND to V _{CC}	0.5V _{CC}	0.5V _{CC}	
74AHCT14	GND to 3.0 V	1.5 V	0.5V _{CC}	

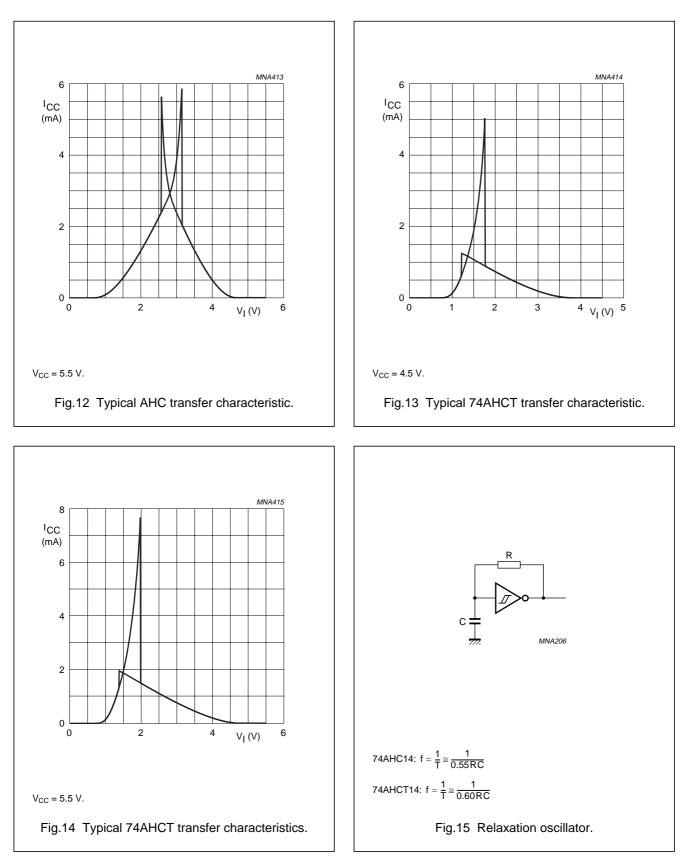
Fig.6 The input (nA) to output (nY) propagation delays.



74AHC14; 74AHCT14



TRANSFER CHARACTERISTIC WAVEFORMS



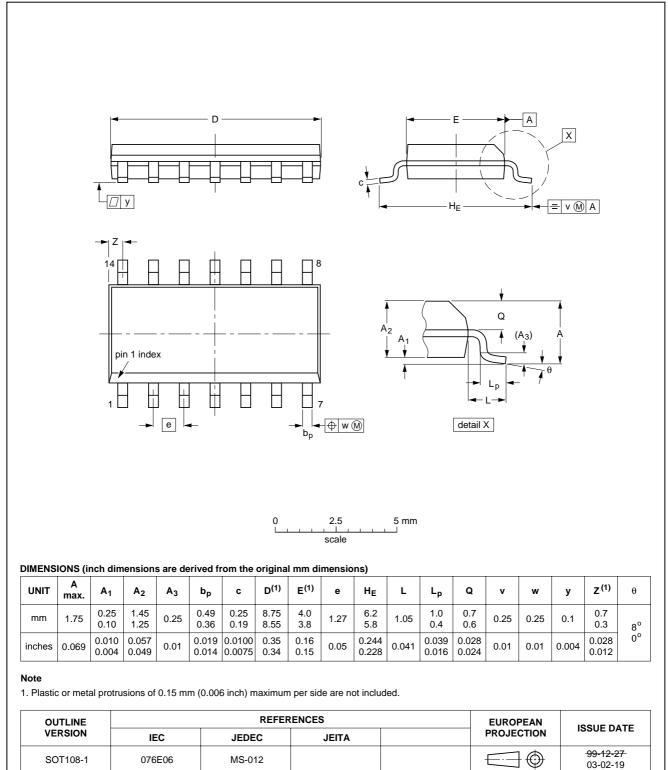
SOT108-1

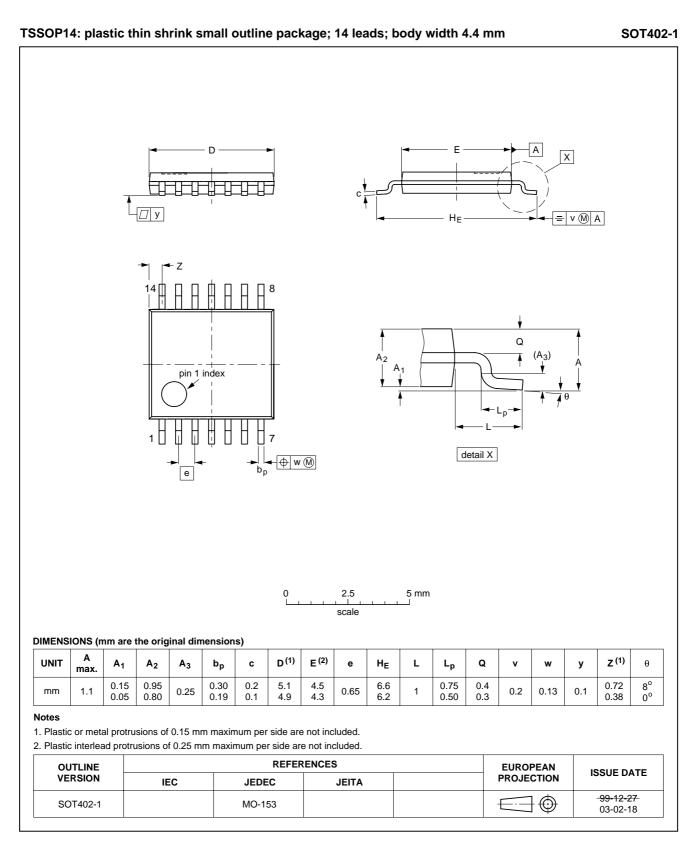
Hex inverting Schmitt trigger

74AHC14; 74AHCT14

PACKAGE OUTLINES

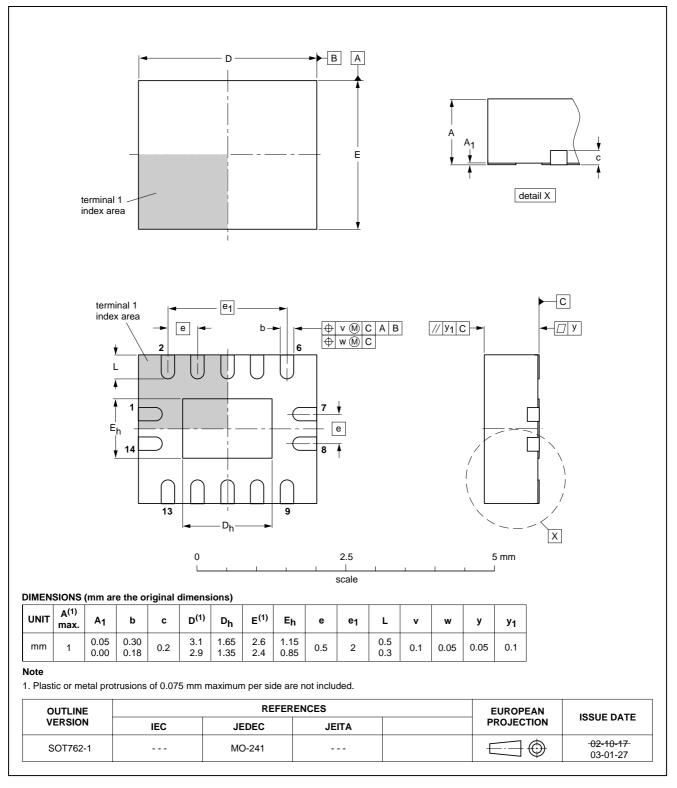






74AHC14; 74AHCT14

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1



SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement. Driven by legislation and environmental forces the worldwide use of lead-free solder pastes is increasing.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 270 °C depending on solder paste material. The top-surface temperature of the packages should preferably be kept:

- below 220 °C (SnPb process) or below 245 °C (Pb-free process)
 - for all the BGA packages
 - for packages with a thickness \geq 2.5 mm
 - − for packages with a thickness < 2.5 mm and a volume \ge 350 mm³ so called thick/large packages.
- below 235 °C (SnPb process) or below 260 °C (Pb-free process) for packages with a thickness < 2.5 mm and a volume < 350 mm³ so called small/thin packages.

Moisture sensitivity precautions, as indicated on packing, must be respected at all times.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems. To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time of the leads in the wave ranges from 3 to 4 seconds at 250 °C or 265 °C, depending on solder material applied, SnPb or Pb-free respectively.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^\circ C.$

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Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE ⁽¹⁾	SOLDERING METHOD		
	WAVE	REFLOW ⁽²⁾	
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable	
DHVQFN, HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽³⁾	suitable	
PLCC ⁽⁴⁾ , SO, SOJ	suitable	suitable	
LQFP, QFP, TQFP	not recommended ⁽⁴⁾⁽⁵⁾	suitable	
SSOP, TSSOP, VSO, VSSOP	not recommended ⁽⁶⁾	suitable	

Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 6. Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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